

# Long Zheng

## List of Publications by Year in descending order

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16  
papers

186  
citations

933447

10  
h-index

1058476

14  
g-index

16  
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16  
docs citations

16  
times ranked

168  
citing authors

#	ARTICLE	IF	CITATIONS
1	Designing artificial carbon clusters using Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> /C superlattice-like structure for phase change applications. <i>Journal of Alloys and Compounds</i> , 2021, 882, 160695.	5.5	13
2	Impact of atomic vacancy on phase change and structure in Ge <sub>x</sub> Te <sub>1-x</sub> films. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 5936-5940.	2.2	2
3	Chromium doped GeTe for low-power-consumption phase change memory. <i>EPJ Applied Physics</i> , 2020, 92, 30101.	0.7	3
4	Designing Multiple Crystallization in Superlattice-like Phase-Change Materials for Multilevel Phase-Change Memory. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 45885-45891.	8.0	20
5	Layer thickness dependence of the phase separation and phase change properties of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> /TiN superlattice-like thin films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2018, 238-239, 71-75.	3.5	4
6	The microstructural changes of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> thin film during crystallization process. <i>AIP Advances</i> , 2018, 8, .	1.3	21
7	Improvement in reliability and power consumption based on Ge <sub>10</sub> Sb <sub>90</sub> films through erbium doping. <i>Journal of Materials Science</i> , 2017, 52, 5216-5222.	3.7	16
8	Superlattice-like Ga <sub>40</sub> Sb <sub>60</sub> /Sb films with ultra-high speed and low power for phase change memory application. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 3806-3811.	2.2	9
9	O-Doped Sb <sub>70</sub> Se <sub>30</sub> Phase-Change Materials for High Thermal Stability and Fast Speed. <i>Journal of Electronic Materials</i> , 2017, 46, 6811-6816.	2.2	12
10	The improvement of phase-change properties on Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> using the superlattice-like structure. <i>EPJ Applied Physics</i> , 2017, 80, 30101.	0.7	2
11	Interface effect and stress effect on Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> /Sb superlattice-like thin films. <i>EPJ Applied Physics</i> , 2017, 77, 30102.	0.7	15
12	Simultaneous thermal stability and phase change speed improvement of Sn <sub>15</sub> Sb <sub>85</sub> thin film through erbium doping. <i>Journal of Applied Physics</i> , 2016, 120, .	2.5	18
13	Improvement of the thermal stability of Sb thin film through erbium doping. <i>CrystEngComm</i> , 2016, 18, 6365-6369.	2.6	26
14	High speed and low power consumption of superlattice-like Ge/Sb <sub>70</sub> Se <sub>30</sub> thin films for phase change memory application. <i>Journal of Materials Science: Materials in Electronics</i> , 2016, 27, 2183-2188.	2.2	14
15	Structure study on SrRu <sub>1-x</sub> Mn <sub>x</sub> O <sub>4</sub> using the extended X-ray absorption fine structure spectroscopy. <i>Journal of X-Ray Science and Technology</i> , 2015, 23, 611-616.	1.0	0
16	N-doped Zn <sub>15</sub> Sb <sub>85</sub> phase-change materials for higher thermal stability and lower power consumption. <i>Journal of Materials Science: Materials in Electronics</i> , 2014, 25, 2943-2947.	2.2	11